

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI ULBM0.5** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.4 A
V_{CB0}	28 V
V_{CEO}	12 V
V_{EBO}	4.0 V
P_{DISS}	2.5 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	70 °C/W

PACKAGE STYLE .205 4L PILL

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.00 / 25.400
B	.976 / 24.800	1.00 / 25.400
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.106 / 2.700	.139 / 3.400
F	.039 / 1.000	.047 / 1.200
G	.004 / 0.100	.006 / 0.150
H	.200 / 5.100	.208 / 5.300

ORDER CODE: ASI10674

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 25 mA	12			V
BV_{CES}	I _C = 10 mA	28			V
BV_{EBO}	I _E = 5.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 150 mA	20		---	---
C_{ob}	V _{CB} = 12.5 V f = 1.0 MHz			4.0	pF
P_G	V _{CC} = 12.5 V P _{OUT} = 0.5 W f = 470 MHz	13			dB